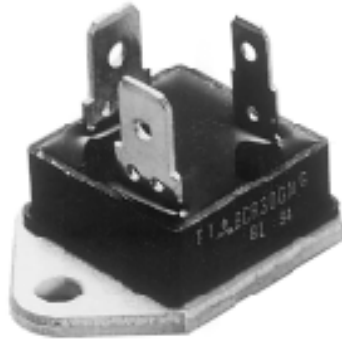


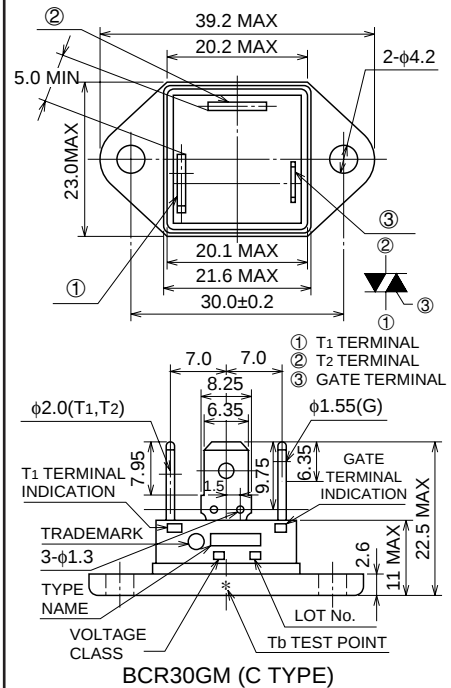
BCR30GM

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- ## OUTLINE DRAWING

Dimensions
in mm



Symbol	Parameter	Voltage class		Unit
		8	12	
V _{DRM}	Repetitive peak off-state voltage *1	400	600	V
V _{DSM}	Non-repetitive peak off-state voltage *1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
I _T (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, T _b =60°C	30	A
I _{TSM}	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	300	A
I ² _t	I ² _t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	375	A ² s
P _{GM}	Peak gate power dissipation		5	W
P _G (AV)	Average gate power dissipation		0.5	W
V _{GM}	Peak gate voltage		10	V
I _{GM}	Peak gate current		2	A
T _j	Junction temperature		-40 ~ +125	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
—	Mounting torque	Screw M4	15	kg·cm
			1.47	N·cm
—	Weight	Typical value	26	g
V _{iso}	Isolation voltage	T _a =25°C, AC 1 minute, T ₂ · T ₁ · G terminal to base	2200	V

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MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDRM	Repetitive peak off-state current	T _J =125°C, V _{DRM} applied	—	—	3.0	mA
V _{TM}	On-state voltage	T _b =25°C, I _{TM} =45A, Instantaneous measurement	—	—	1.6	V
V _{FGT} I	Gate trigger voltage *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	—	—	2.5	V
V _{RGT} I			—	—	2.5	V
V _{RGT} III			—	—	2.5	V
I _{FGT} I	Gate trigger current *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	—	—	50	mA
I _{RGT} I			—	—	50	mA
I _{RGT} III			—	—	50	mA
V _{GD}	Gate non-trigger voltage	T _J =125°C, V _D =1/2V _{DRM}	0.2	—	—	V
R _{th} (j-b)	Thermal resistance	Junction to base *4	—	—	1.6	°C/W
(dv/dt) _c	Critical-rate of rise of off-state commutating voltage		*3	—	—	V/μs

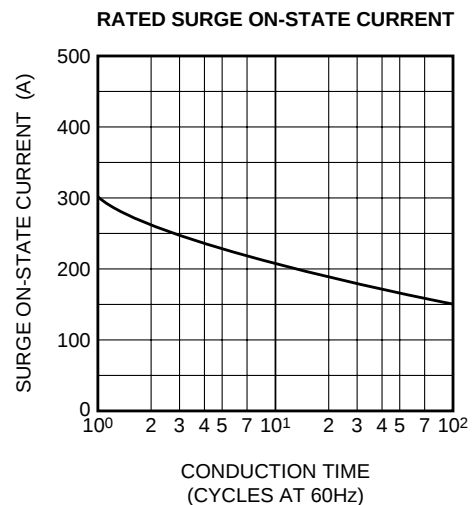
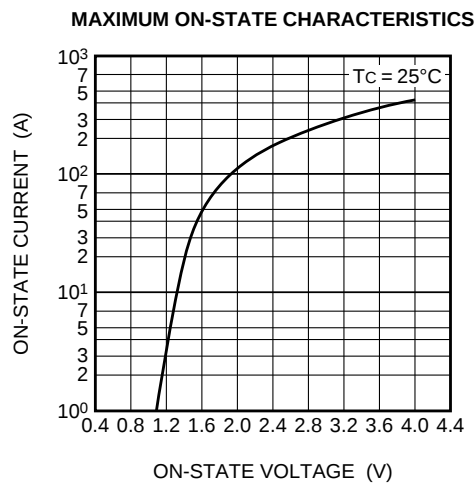
*2. Measurement using the gate trigger characteristics measurement circuit.

*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.

*4. The contact thermal resistance R_{th} (b-f) in case of greasing is 0.5°C/W.

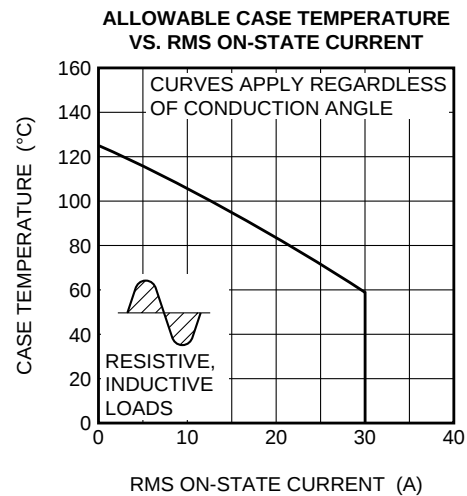
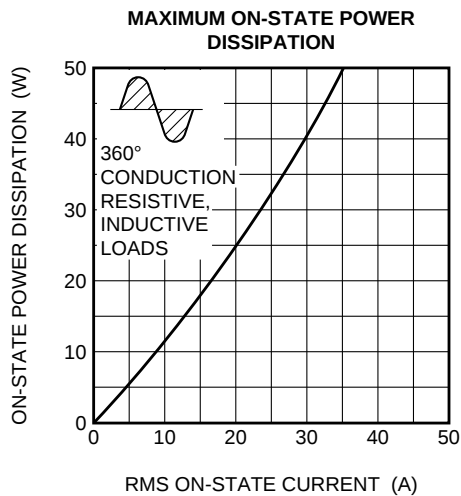
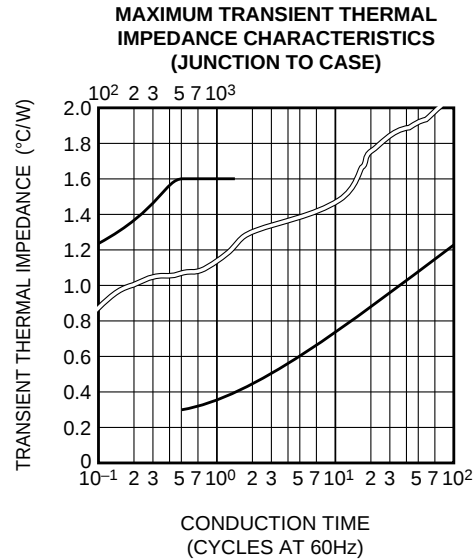
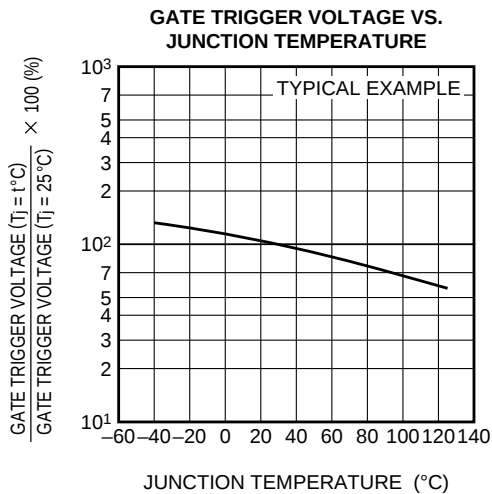
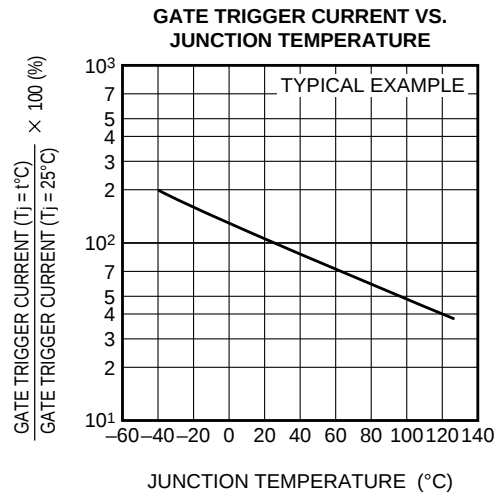
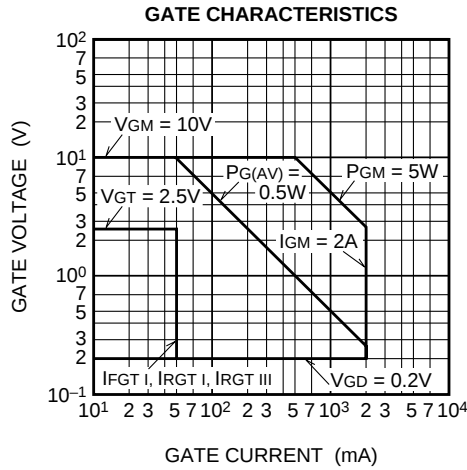
Voltage class	V _{DRM} (V)	(dv/dt) _c			Test conditions	Commutating voltage and current waveforms (inductive load)
		Symbol	Min.	Unit		
8	400	R	—	V/μs	1. Junction temperature T _J =125°C 2. Rate of decay of on-state commutating current (di/dt) _c =-16A/ms 3. Peak off-state voltage V _D =400V	
		L	20			
12	600	R	—			
		L	20			

PERFORMANCE CURVES



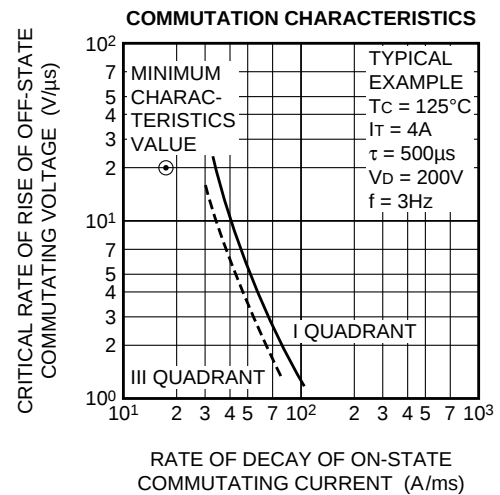
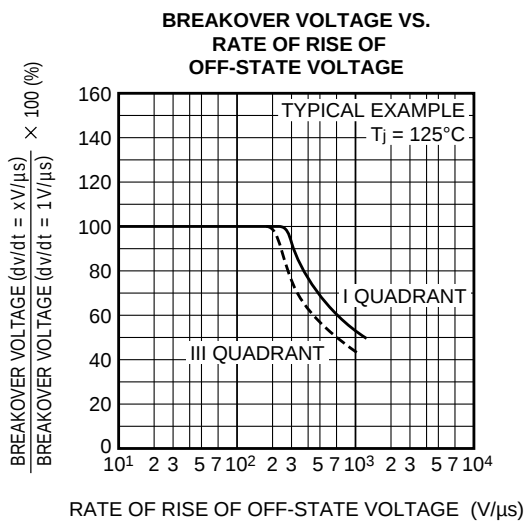
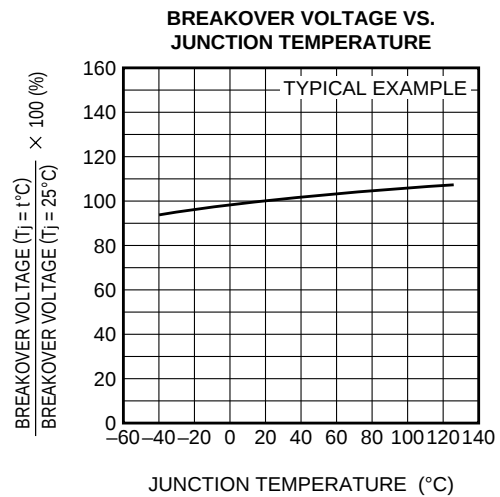
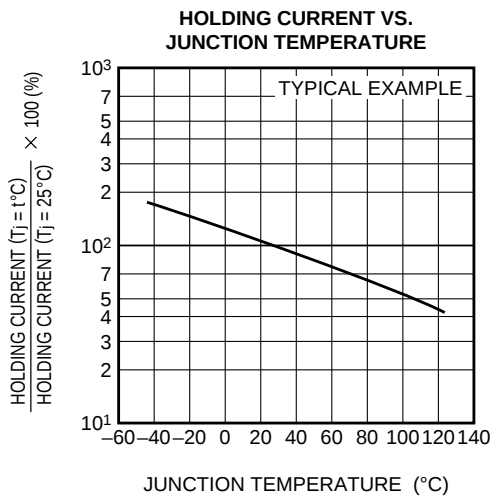
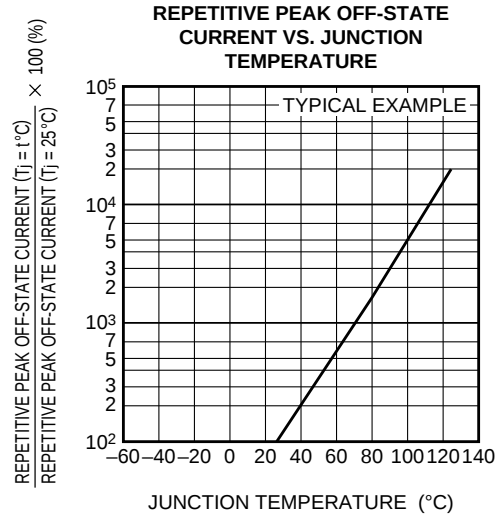
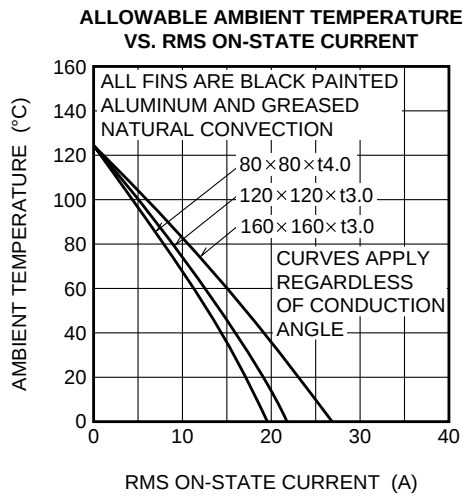
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MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE



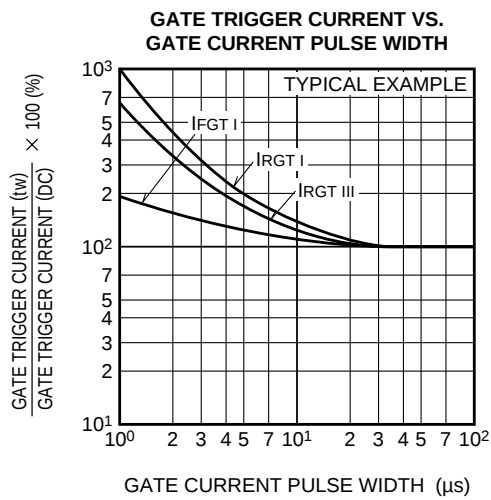
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MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE



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MEDIUM POWER USE
INSULATED TYPE, GLASS PASSIVATION TYPE



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

